

THYRISTOR(Surface Mount Device/Non-isolated)

SMG08C60A

(Sensitive Gate)

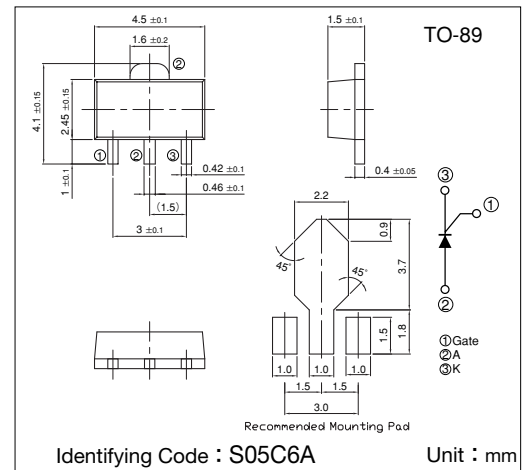
SanRex Thyristor SMG05C60A is designed for full wave AC control applications. It can be used as an ON/OFF function or for phase control operation.

Typical Applications

- Home Appliances : Electric Blankets, Starter for FL, other control applications
- Industrial Use : SMPS, Solenoid for Breakers, Motor Controls, Heater Controls, other control applications

Features

- $I_{T(AV)}=0.5A$
- High Surge Current
- Lead-Free Package



Maximum Ratings

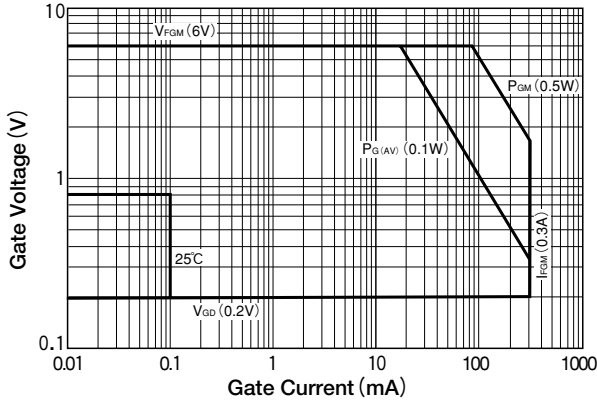
($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Item	Reference	Ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage		720	V
V_{DRM}	Repetitive Peak Off-State Voltage		600	V
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, 180° , conduction, $T_c=46^\circ\text{C}$	0.8	A
$I_{T(RMS)}$	R.M.S. On-State Current	Single phase, half wave, 180° , conduction, $T_c=46^\circ\text{C}$	1.3	A
I_{TSM}	Surge On-State Current	50Hz/60Hz, $\frac{1}{2}$ cycle Peak value, non-repetitive	18/20	A
I^2t	I^2t		1.65	A^2S
P_{GM}	Peak Gate Power Dissipation		0.5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.1	W
I_{FGM}	Peak Gate Current		0.3	A
V_{FGM}	Peak Gate Voltage (Forward)		6	V
V_{RGM}	Peak Gate Voltage (Reverse)		6	V
T_j	Operating Junction Temperature		$-40 \sim +125$	$^\circ\text{C}$
T_{stg}	Storage Temperature		$-40 \sim +150$	$^\circ\text{C}$
	Mass		0.05	g

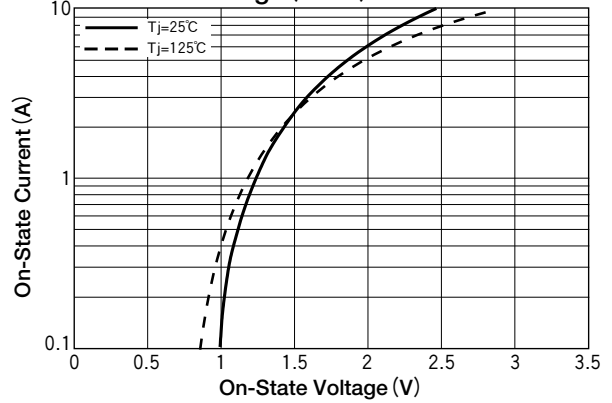
Electrical Characteristics

Symbol	Item	Reference	Ratings			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive Peak Off-State Current	$T_j=125^\circ\text{C}$, $V_D=V_{DRM}$, $R_{GK}=1k\Omega$			0.5	mA
I_{RRM}	Repetitive Peak Reverse Current	$T_j=125^\circ\text{C}$, $V_R=V_{RRM}$, $R_{GK}=1k\Omega$			0.5	mA
V_{TM}	Peak On-State Voltage	$I_T=2.5A$, Inst. measurement			1.5	V
I_{GT}	Gate Trigger Current	$V_D=6V$, $R_L=100\Omega$			100	μA
V_{GT}	Gate Trigger Voltage				0.8	V
V_{GD}	Non-Trigger Gate Voltage	$T_j=125^\circ\text{C}$, $V_D=\frac{1}{2}V_{DRM}$, $R_{GK}=1k\Omega$	0.2			V
I_H	Holding Current			300		μA
$R_{th(j-a)}$	Thermal Resistance	Junction to ambient			65	$^\circ\text{C/W}$

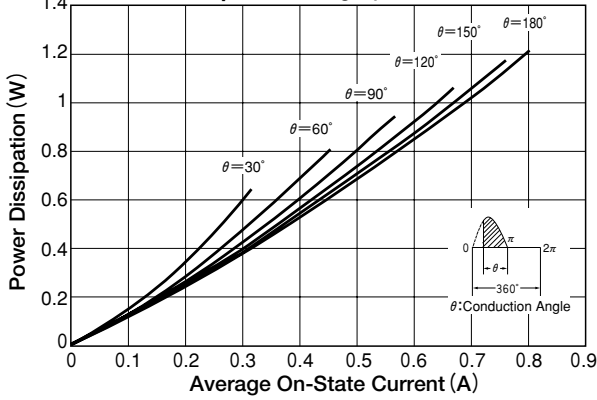
Gate Characteristics



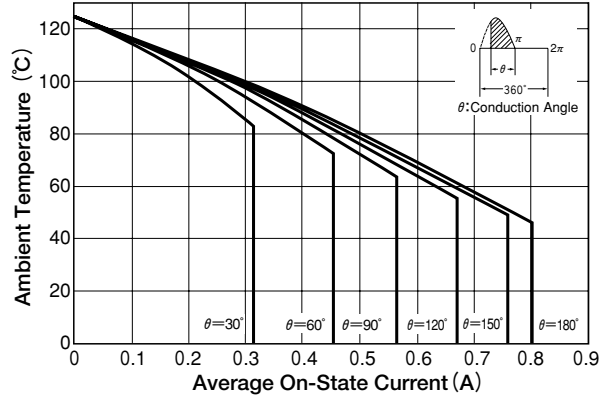
On-State Voltage (MAX)



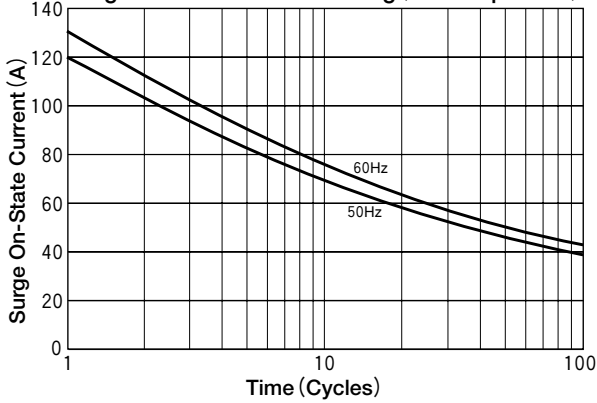
Average On-State Current vs Power Dissipation (Single phase half wave)



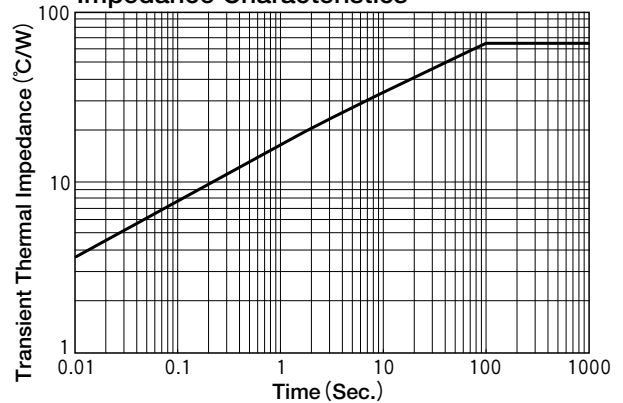
Average On-State Current vs Ambient Temperature (Single phase half wave)



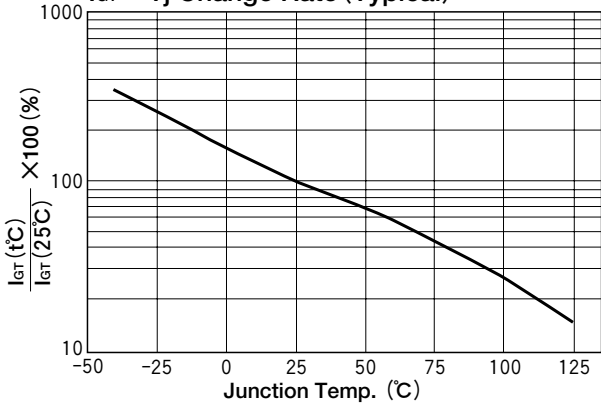
Surge On-State Current Rating (Non-Repetitive)



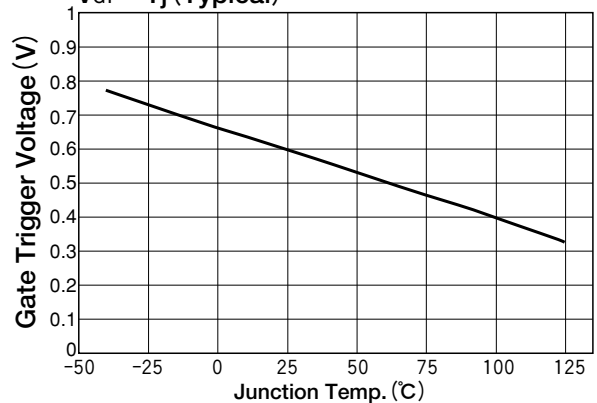
Maximum Transient Thermal Impedance Characteristics



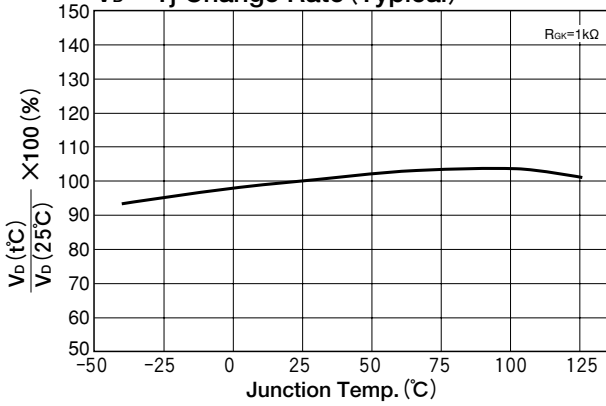
I_{GT} - T_j Change Rate (Typical)



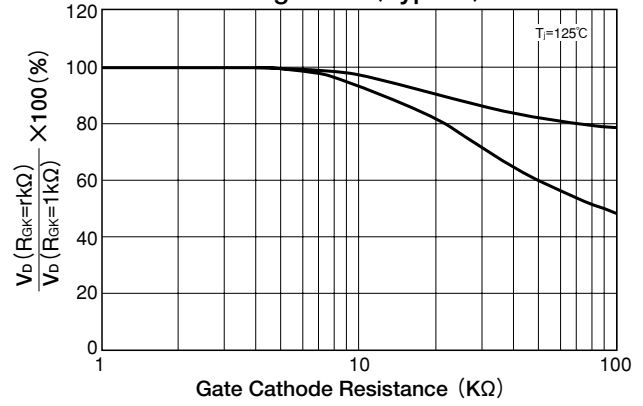
V_{GT} - T_j (Typical)



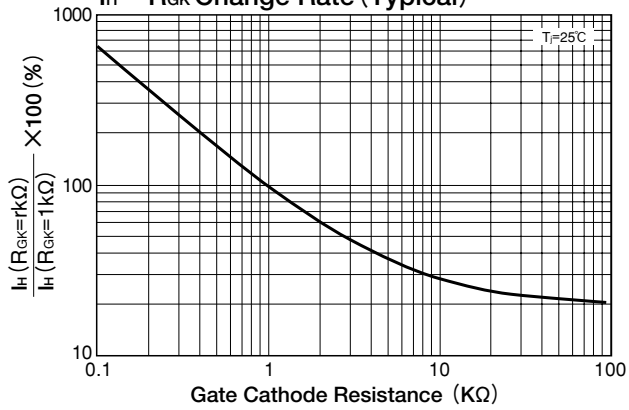
V_D — T_j Change Rate (Typical)



V_D — R_{GK} Change Rate (Typical)



I_H — R_{GK} Change Rate (Typical)



V_R — T_j Change Rate (Typical)

